Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt[®]



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TO-220 FullPAK 2L

PRIMARY CHARACTERISTICS					
I _{F(AV)}	30 A				
V _R	600 V				
V _F at I _F	1.34 V				
t _{rr} (typ.)	23 ns				
T _J max.	175 °C				
Package	TO-220 FullPAK 2L				
Circuit configuration	Single				

FEATURES

- Reduced Q_{rr} and soft recovery
- 175 °C T_{.1} maximum
- For PFC CRM/CCM operation
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- · Designed and qualified according to JEDEC[®]-JESD 47



COMPLIANT HALOGEN FREE

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	V _{RRM}		600	V		
Average rectified forward current	I _{F(AV)}	T _C = 37 °C	30	٨		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	220	A		
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
Forward voltage V _F		I _F = 30 A	-	2.00	2.60	V		
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75			
Deverse leekees surrent	1	$V_R = V_R$ rated	-	0.3	50			
Reverse leakage current I _R		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	60	500	μA		
Junction capacitance	CT	V _R = 600 V	-	33	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH		

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$	0 A/µs, V _R = 30 V	-	28	35		
Povereo recover time	+	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_H$	00 A/µs, V _R = 30 V	-	23	30	ns	
Reverse recovery time t _{rr}	۲r	T _J = 25 °C		-	31	-		
		T _J = 125 °C		-	77	-		
Dook roooyon, ourront	1	T _J = 25 °C	$I_F = 30 A$	-	3.5	-	А	
Peak recovery current I _{RRM}	IRRM	T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 200 V	-	7.7	-	A	
Reverse recovery charge C	$Q_{rr} \qquad \frac{T_J = 25 \text{ °C}}{T_J = 125 \text{ °C}}$	0	T _J = 25 °C		-	65	-	
			-	345	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case per leg	R _{thJC}		-	-	2.85		
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.2	-		
Weight			-	2	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220 FullPAK 2L		30ETH	H06FP		



VS-30ETH06FP-N3

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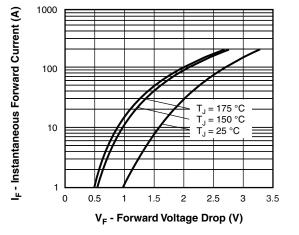


Fig. 1 - Typical Forward Voltage Drop Characteristics

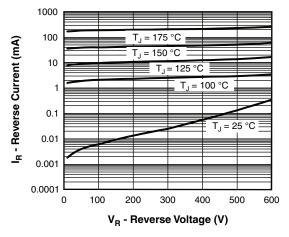


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

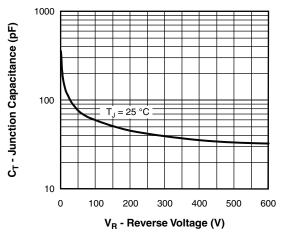
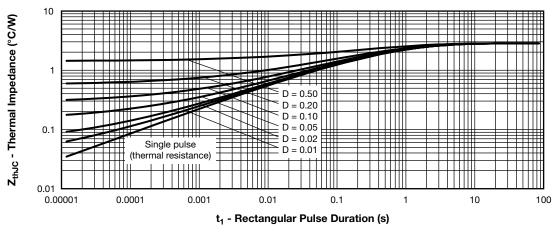


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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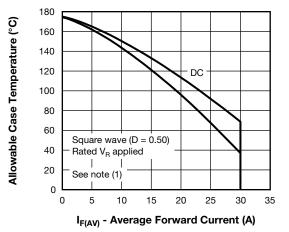


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

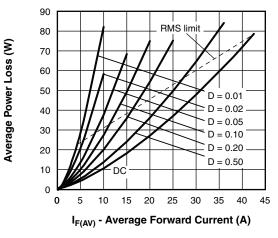


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

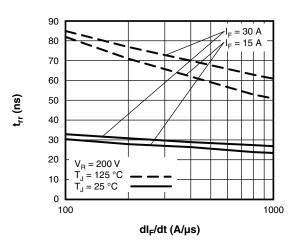


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

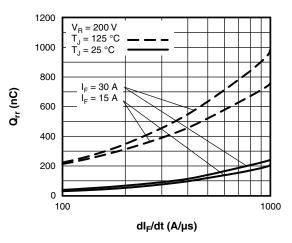


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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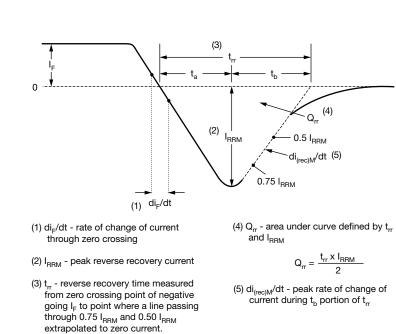


Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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Device code	VS-	30	Е	т	н	06	FP	-N3
		2	3	4	5	6	7	8
	1	- Vis	hay Ser	nicondu	ctors pro	oduct		
	2	- Cui	rent rat	ing (30 /	A)			
	3	- E=	single	diode				
	4	- T=	TO-220)				
	5	- H=	hyperfa	ast recov	very			
	6	- Vol	tage rat	ing (06 =	= 600 V))		
	7	- Ful	IPAK					
	8	- Env	vironme	ntal digit				
		-N3	= halog	gen-free	, RoHS-	complia	ant, and	totally I

ORDERING INFORMATION (Example)							
PREFERRED P/N	EFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-30ETH06FP-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96157				
Part marking information	www.vishay.com/doc?95392				

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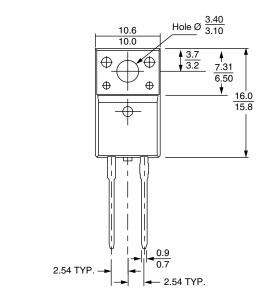
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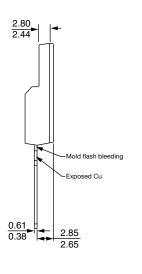


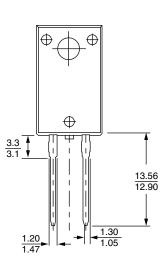
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2L TO-220 FullPAK

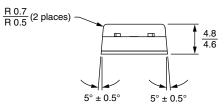
DIMENSIONS in millimeters







Bottom view





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